

RJH60D5DPK

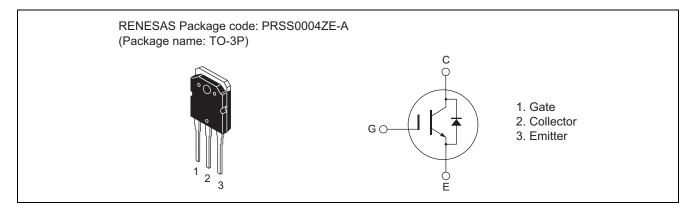
Silicon N Channel IGBT Application: Inverter

REJ03G1846-0100 Rev.1.00 Oct 14, 2009

Features

- High breakdown-voltage
- Low on-voltage
- Built-in diode

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item		Symbol	Ratings	Unit
Collector to emitter voltage / diode reverse voltage		V _{CES} / V _R	600	V
Gate to emitter voltage		V_{GES}	±30	V
Collector current	Tc = 25°C	Ic	60	Α
	Tc = 100°C	Ic	30	Α
Collector peak current		ic(peak) Note1	120	Α
Collector to emitter diode forward current		I _{DF}	30	Α
Collector to emitter diode forward peak current		i _{DF} (peak) Note1	120	Α
Collector dissipation		P _C Note2	200	W
Junction to case thermal impedance		θj-c ^{Note2}	0.63	°C/W
Junction temperature		Tj	150	°C
Storage temperature		Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

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Electrical Characteristics

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 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Zero gate voltage collector current / Diode reverse current	I _{CES} / I _R	_	_	100	μА	V _{CE} = 600 V, V _{GE} = 0
Gate to emitter leak current	I _{GES}	_	_	±1	μА	$V_{GE} = \pm 30 \text{ V}, V_{CE} = 0$
Gate to emitter cutoff voltage	$V_{GE(off)}$	4.0	_	6.0	V	V _{CE} = 10 V, I _C = 1 mA
Collector to emitter saturation voltage	V _{CE(sat)}	_	1.6	2.2	V	$I_C = 30 \text{ A}, V_{GE} = 15 \text{ V}^{\text{Note3}}$
	V _{CE(sat)}	_	1.8	_	V	$I_C = 60 \text{ A}, V_{GE} = 15 \text{ V}^{\text{Note3}}$
Input capacitance	Cies	_	1900	_	pF	V _{CE} = 25 V
Output capacitance	Coes	_	130	_	pF	V _{GE} = 0
Reveres transfer capacitance	Cres	_	60		pF	f = 1 MHz
Total gate charge	Qg	_	79	_	nC	V _{GE} = 15 V
Gate to emitter charge	Qge	_	11	_	nC	V _{CE} = 300 V
Gate to collector charge	Qgc	_	33	_	nC	I _C = 30 A
Switching time	t _{d(on)}	_	45	_	ns	I _C = 30 A
	t _r	_	65	_	ns	$R_L = 10 \Omega$
	t _{d(off)}	_	125	_	ns	V _{GE} = 15 V
	t _f	_	75	_	ns	Rg = 5 Ω
FRD Forward voltage	V _F		1.8		V	I _F = 30 A ^{Note3}
TILD I OIWald Vollage	٧F		1.0		٧	IF - 00 A

100

ns

 $I_F = 30 A$

 $di_F/dt = 100 A/\mu s$

Notes: 3. Pulse test.

FRD reverse recovery time

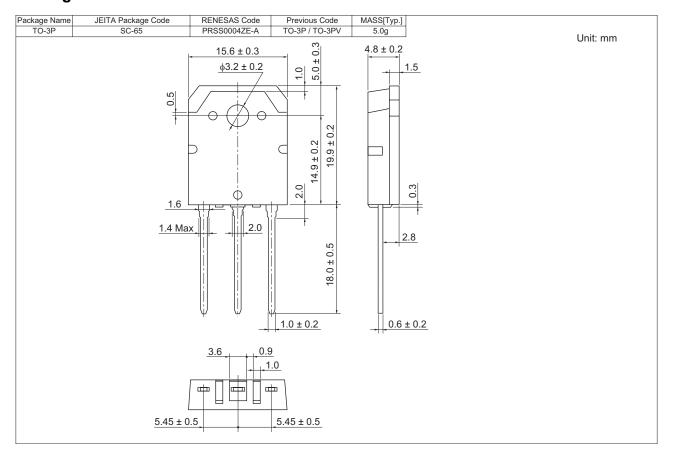
4. Under development. –The specifications potentially be changed without notice.

 t_{rr}

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Package Dimension

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Ordering Information

Part No.	Quantity	Shipping Container
RJH60D5DPK-00-T0	360 pcs	Box (Tube)

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- Notes:

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